

DERWENT-ACC-NO: 2003-226914

DERWENT-WEEK: 200442

COPYRIGHT 2005 DERWENT INFORMATION LTD

TITLE: Method for manufacturing semiconductor device

INVENTOR: OH, S H

PATENT-ASSIGNEE: ANAM SEMICONDUCTOR LTD[ANAMN] , ANAM SEMICONDUCTOR  
TECHNOLOGY CO LTD[ANAMN]

PRIORITY-DATA: 2001KR-0025683 (May 11, 2001)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE
PAGES MAIN-IPC		
KR 419786 B	February 21, 2004	N/A
000 H01L 021/3213		
KR 2002086042 A	November 18, 2002	N/A
001		

H01L 021/3213

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
APPL-DATE		
KR 419786B	N/A	2001KR-0025683
May 11, 2001		
KR 419786B	Previous Publ.	KR2002086042
N/A		
KR2002086042A	N/A	2001KR-0025683
May 11, 2001		

INT-CL (IPC): H01L021/3213

ABSTRACTED-PUB-NO: KR2002086042A

BASIC-ABSTRACT:

NOVELTY - A fabrication method of a semiconductor device is provided to prevent an erosion of metal interconnections by dry-cleaning using a gas of fluoride(F) series after etching a metal film.

DETAILED DESCRIPTION - An oxide layer(11) is deposited on a semiconductor substrate(10). A metal film, such as aluminum or aluminum alloy is deposited on the oxide layer(11). After forming a photoresist pattern on the resultant structure, a metal pattern(120) is formed by selectively etching the exposed metal film using chlorinated mixed gases. Cl2 gas and BCl3 gas are used as the Chlorinated mixed gases. Then, the resultant structure is dry-cleaned by using a gas of fluoride(F) series. Preferably, CHF3 gas is used as the gas of fluoride(F) series. At this time, argon(Ar) gas is mixed to the gas of fluoride(F) series.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: METHOD MANUFACTURE SEMICONDUCTOR DEVICE

DERWENT-CLASS: L03 U11

CPI-CODES: L04-C06B1; L04-C07B; L04-C09; L04-C10C; L04-C12A;

EPI-CODES: U11-C05D3; U11-C07C2;

SECONDARY-ACC-NO:

CPI Secondary Accession Numbers: C2003-058187